

Discrete POWER & Signal **Technologies**

2N7052

2N7053

NZT7053







NPN Darlington Transistor

This device is designed for applications requiring extremely high gain at collector currents to 1.0 A and high breakdown voltage. Sourced from Process 06.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	100	V
V _{CBO}	Collector-Base Voltage	100	V
V_{EBO}	Emitter-Base Voltage	12	V
Ic	Collector Current - Continuous	1.5	Α
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max			Units
		2N7052	2N7053	*NZT7053	
P _D	Total Device Dissipation	625	1,000	1,000	mW
	Derate above 25°C	5.0	8.0	8.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	125		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	50	125	°C/W

Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm².

These ratings are based on a maximum junction temperature of 150 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

NPN Darlington Transistor

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TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	100		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	100		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 1.0 \text{ mA}, I_C = 0$	12		V
I _{CBO}	Collector-Cutoff Current	$V_{CB} = 80 \text{ V}, I_{E} = 0$		0.1	μΑ
I _{CES}	Collector-Cutoff Current	$V_{CE} = 80 \text{ V}, I_{E} = 0$		0.2	μΑ
I _{EBO}	Emitter-Cutoff Current	$V_{EB} = 7.0 \text{ V}, I_{C} = 0$		0.1	μΑ

ON CHARACTERISTICS*

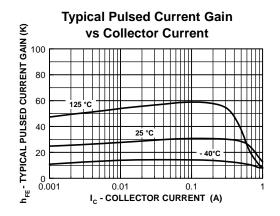
h _{FE}	DC Current Gain	$I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$	10,000		
		$I_C = 1.0 \text{ A}, V_{CE} = 5.0 \text{ V}$	1,000	20,000	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 100 \text{ mA}, I_B = 0.1 \text{ mA}$		1.5	V
V _{BE(on)}	Base-Emitter On Voltage	$I_C = 100 \text{ mA}, V_{BE} = 5.0 \text{ V}$		2.0	V

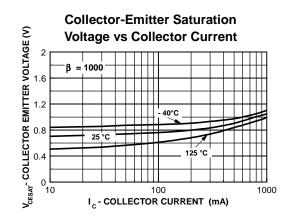
SMALL SIGNAL CHARACTERISTICS

F _T	Transition Frequency	$I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V},$	200		MHz
C _{cb}	Collector-Base Capacitance	V _{CB} = 10 V,f = 1.0 MHz 2N7052		10	pF
		2N7053		8.0	

^{*}Pulse Test: Pulse Width £ 300 ms, Duty Cycle £ 1.0%

Typical Characteristics

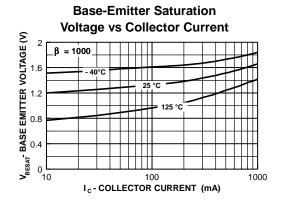


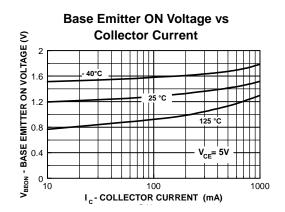


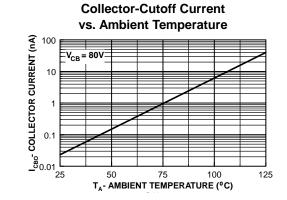
NPN Darlington Transistor

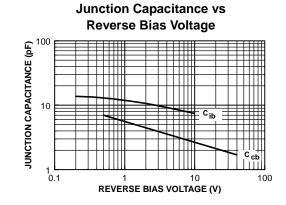
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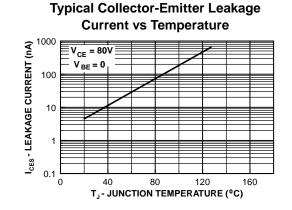
Typical Characteristics (continued)

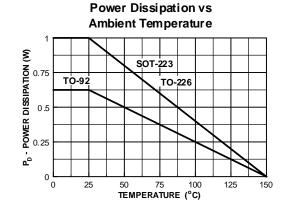










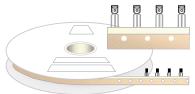


TO-92 Tape and Reel Data FAIRCHILD SEMICONDUCTOR TM **TO-92 Packaging** Configuration: Figure 1.0 **TAPE and REEL OPTION** FSCINT Label sample See Fig 2.0 for various Reeling Styles CBVK//418019 **FSCINT** Label 5 Reels per Intermediate Box Customized F63TNR Label sample Label F63TNR LOT: CBVK741B019 QTY: 2000 FSID: PN222N Customized QTY1: QTY2: 375mm x 267mm x 375mm Intermediate Box TO-92 TNR/AMMO PACKING INFROMATION **AMMO PACK OPTION** See Fig 3.0 for 2 Ammo Packing Style Quantity EOL code **Pack Options** 2,000 D26Z Е 2,000 D27Z Ammo М 2,000 D74Z 2,000 D75Z **FSCINT** Unit weight = 0.22 gm Reel weight with components = 1.04 kg Ammo weight with components = 1.02 kg Max quantity per intermediate box = 10,000 units Label 5 Ammo boxes per Intermediate Box 327mm x 158mm x 135mm Immediate Box Customized F63TNR Customized Label Label 333mm x 231mm x 183mm Intermediate Box (TO-92) BULK PACKING INFORMATION **BULK OPTION** See Bulk Packing DESCRIPTION QUANTITY Information table J18Z TO-18 OPTION STD 2.0 K / BOX Anti-static Bubble Sheets TO-5 OPTION STD NO LEAD CLIP 1.5 K / BOX J05Z **FSCINT Label** NO EOL TO-92 STANDARD STRAIGHT FOR: PKG 92, NO LEADCLIP 2.0 K / BOX 94 (NON PROELECTRON SERIES), 96 TO-92 STANDARD STRAIGHT FOR: PKG 94 (PROELECTRON SERIES BCXXX, BFXXX, BSRXXX), 97, 98 L34Z NO LEADCLIP 2.0 K / BOX 2000 units per 114mm x 102mm x 51mm EO70 box for std option Immediate Box 5 EO70 boxes per intermediate Box 530mm x 130mm x 83mm Customized Intermediate box Label FSCINT Label 10,000 units maximum per intermediate box for std option

TO-92 Tape and Reel Data, continued

TO-92 Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)

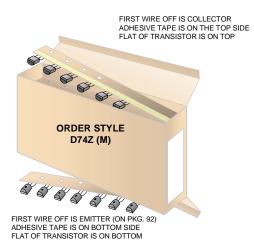


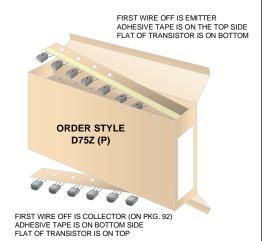
Style "A", D26Z, D70Z (s/h)

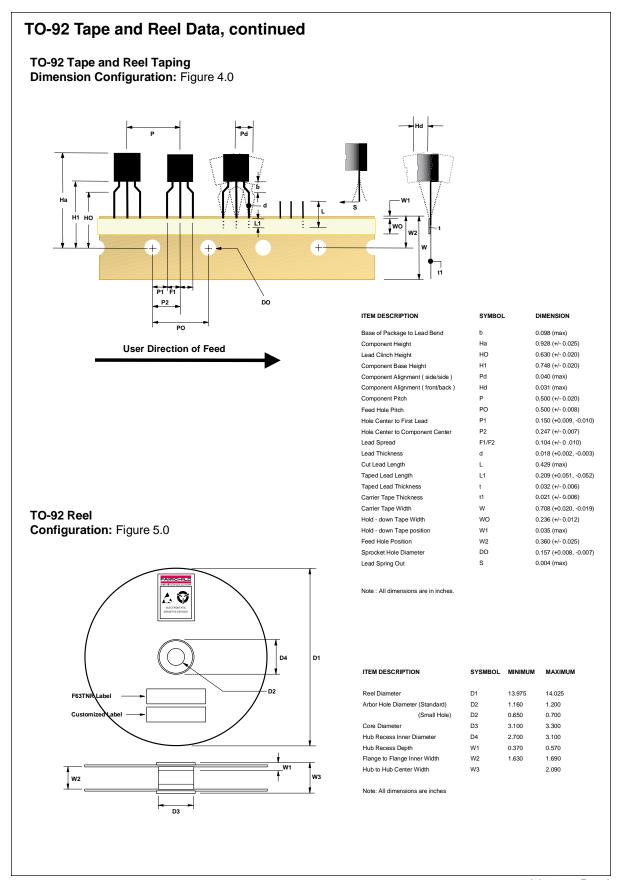
Machine Option "E" (J)

Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging Configuration: Figure 3.0



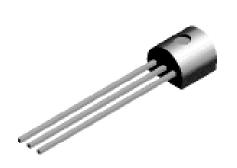


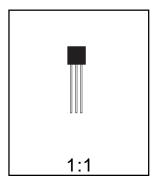


TO-92 Package Dimensions



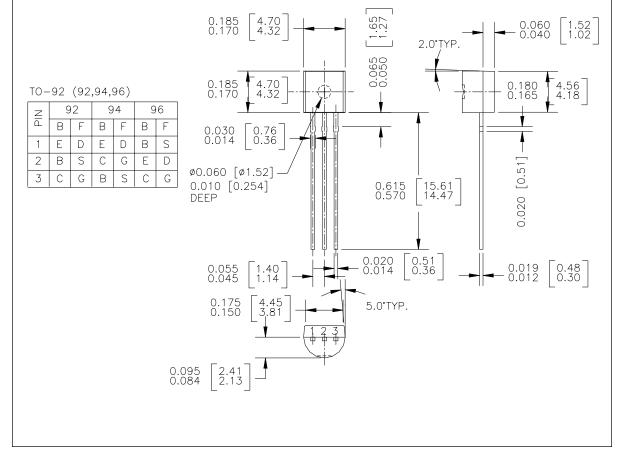
TO-92 (FS PKG Code 92, 94, 96)





Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977



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